

T-46-07-U

573



54FCT/74FCT573

Octal Latch with TRI-STATE® Outputs

General Description

The 'FCT573 is a high-speed octal latch with buffered common Latch Enable (LE) and buffered common Output Enable (OE) inputs.

FACT™ FCT utilizes NSC quiet series technology to provide improved quiet output switching and dynamic threshold performance.

FACT FCT features GTOT™ output control and undershoot corrector in addition to a split ground bus for superior performance.

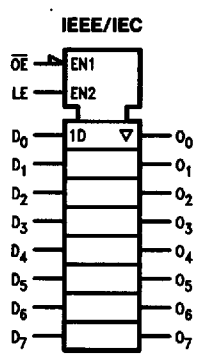
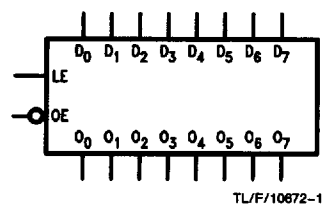
The 'FCT573 is functionally identical to the 'FCT373 but has inputs and outputs on opposite sides.

Features

- I_{CC} and I_{OZ} reduced to 40.0 μA and $\pm 25 \mu A$ respectively
- NSC 54/74FCT573 is pin and functionally equivalent to IDT 54/74FCT573
- TRI-STATE outputs for bus interfacing
- Input clamp diodes to limit bus reflections
- TTL/CMOS input and output level compatible
- $I_{OL} = 48 \text{ mA (Com)}, 32 \text{ mA (Mil)}$
- CMOS power levels
- ESD immunity $\geq 4 \text{ kVp}$
- Military Product compliant to MIL-STD-883 and Standard Military Drawing #5962-88639

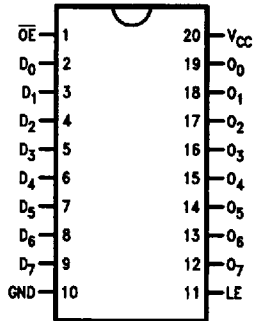
Ordering Code: See Section 8

Logic Symbols



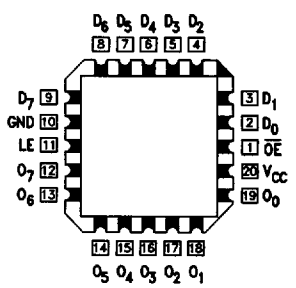
Connection Diagrams

Pin Assignment for DIP, Flatpak and SOIC



Pin Names	Description
D ₀ -D ₇	Data Inputs
LE	Latch Enable Input
OE	TRI-STATE Output Enable Input
O ₀ -O ₇	TRI-STATE Latch Outputs

Pin Assignment for LCC



Functional Description

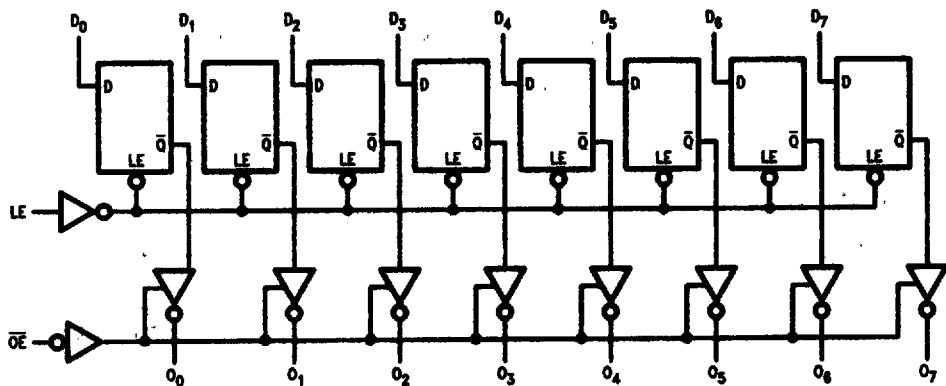
The FCT573 contains eight D-type latches with TRI-STATE output buffers. When the Latch Enable (LE) input is HIGH, data on the D_n inputs enters the latches. In this condition the latches are transparent, and the latch output will change state each time its D input changes. When LE is LOW the latches store the information that was present on the D inputs a setup time preceding the HIGH-to-LOW transition of LE. The TRI-STATE buffers are controlled by the Output Enable (\overline{OE}) input. When \overline{OE} is LOW, the latch contents are presented inverted at the outputs O_7 - O_0 . When \overline{OE} is HIGH the buffers are in the high impedance mode but this does not interfere with entering new data into the latches.

Truth Table

Inputs			Outputs
\overline{OE}	LE	D	O_n
L	H	H	H
L	H	L	L
L	L	X	O_0
H	X	X	Z

H = HIGH Voltage
 L = LOW Voltage
 Z = High Impedance
 X = Immaterial
 O_0 = Previous O_0 before HIGH-to-LOW transition of Latch Enable

Logic Diagram



TL/F/10872-5

Please note that this diagram is provided only for the understanding of logic operations and should not be used to estimate propagation delays.

Absolute Maximum Rating (Note 1)

If Military/Aerospace specified devices are required, please contact the National Semiconductor Sales Office/Distributors for availability and specifications.

Terminal Voltage with Respect to GND (V_{TERM})	
54FCT	-0.5V to +7.0V
74FCT	-0.5V to +7.0V
Temperature under Bias (T_{BIAS})	
54FCT	-65°C to +135°C
74FCT	-55°C to +125°C
Storage Temperature (T_{STG})	
54FCT	-65°C to +150°C
74FCT	-55°C to +125°C
DC Output Current (I_{OJT})	120 mA

Note 1: Absolute maximum ratings are those values beyond which damage to the device may occur. Exposure to absolute maximum rating conditions for extended periods may affect reliability. The databook specifications should be met, without exception, to ensure that the system design is reliable over its power supply, temperature, and output/input loading variables.

Recommended Operating Conditions

Supply Voltage (V_{CC})	4.5V to 5.5V
54FCT	4.75V to 5.25V
74FCT	
Input Voltage	0V to V_{CC}
Output Voltage	0V to V_{CC}
Operating Temperature (T_A)	-55°C to +125°C
54FCT	0°C to +70°C
74FCT	
Junction Temperature (T_J)	
CDIP	175°C
PDIP	140°C

Note: All commercial packaging is not recommended for applications requiring greater than 2000 temperature cycles from -40°C to +125°C.

DC Characteristics for 'FCT Family Devices

Typical values are at $V_{CC} = 5.0V$, 25°C ambient and maximum loading. For test conditions shown as Max, use the value specified for the appropriate device type: Com: $V_{CC} = 5.0V \pm 5\%$, $T_A = 0^\circ C$ to $+70^\circ C$; Mil: $5.0V \pm 10\%$, $T_A = -55^\circ C$ to $+125^\circ C$, $V_{HC} = V_{CC} - 0.2V$

Symbol	Parameter	54FCT/74FCT			Units	Conditions	
		Min	Typ	Max			
V_{IH}	Minimum High Level Input Voltage	2.0			V		
V_{IL}	Maximum Low Level Input Voltage			0.8	V		
I_{IH}	Input High Current			5.0 5.0	μA	$V_{CC} = \text{Max}$	$V_I = V_{CC}$ $V_I = 2.7V$ (Note 2)
I_{IL}	Input Low Current			-5.0 -5.0	μA	$V_{CC} = \text{Max}$	$V_I = 0.5V$ (Note 2) $V_I = GND$
I_{OZ}	Maximum TRI-STATE Current			2.5 2.5 -2.5 -2.5	μA	$V_{CC} = \text{Max}$	$V_O = V_{CC}$ $V_O = 2.7V$ (Note 2) $V_O = 0.5V$ (Note 2) $V_O = GND$
V_{IK}	Clamp Diode Voltage	-0.7	-1.2		V	$V_{CC} = \text{Min}; I_N = -18 \text{ mA}$	
I_{OS}	Short Circuit Current	-60	-120		mA	$V_{CC} = \text{Max}$ (Note 1); $V_O = GND$	
V_{OH}	Minimum High Level Output Voltage	2.8	3.0		V	$V_{CC} = 3V; V_{IN} = 0.2V$ or $V_{HC}; I_{OH} = -32 \mu A$	$I_{OH} = -300 \mu A$ $I_{OH} = -12 \text{ mA}$ (Mil) $I_{OH} = -15 \text{ mA}$ (Com)
		V_{HC}	V_{CC}				
		2.4	4.3				
		2.4	4.3				
V_{OL}	Maximum Low Level Output Voltage	GND	0.2		V	$V_{CC} = 3V; V_{IN} = 0.2V$ or $V_{HC}; I_{OL} = 300 \mu A$	$I_{OL} = 300 \mu A$ $I_{OL} = 32 \text{ mA}$ (Mil) $I_{OL} = 48 \text{ mA}$ (Com)
		GND	0.2				
		0.3	0.50				
		0.3	0.50				
I_{CC}	Maximum Quiescent Supply Current	1.0	40.0		μA	$V_{CC} = \text{Max}$ $V_{IN} \geq V_{HC}, V_{IN} \leq 0.2V$ $f_I = 0$	
ΔI_{CC}	Quiescent Supply Current; TTL Inputs HIGH	0.5	2.0		mA	$V_{CC} = \text{Max}$ $V_{IN} = 3.4V$ (Note 3)	
I_{CCD}	Dynamic Power Supply Current (Note 4)	0.25	0.45		mA/MHz	$V_{CC} = \text{Max}$ Outputs Open One Input Toggling 50% Duty Cycle $\overline{OE} = GND$ $LE = V_{CC}$	$V_{IN} \geq V_{HC}$ $V_{IN} \leq 0.2V$

DC Characteristics for 'FCT Family Devices (Continued)

Typical values are at $V_{CC} = 5.0V$, $25^{\circ}C$ ambient and maximum loading. For test conditions shown as Max, use the value specified for the appropriate device type: Com: $V_{CC} = 5.0V \pm 5\%$, $T_A = 0^{\circ}C$ to $+70^{\circ}C$; Mil: $5.0V \pm 10\%$, $T_A = -55^{\circ}C$ to $+125^{\circ}C$, $V_{HC} = V_{CC} - 0.2V$

Symbol	Parameter	74FCT			Units	Conditions	
		Min	Typ	Max			
I_C	Total Power Supply Current (Note 6)	1.5	4.5		mA	$V_{CC} = \text{Max}$ Outputs Open $OE = GND, LE = V_{CC}$ $f_{CP} = 10 \text{ MHz}$ One Bit Toggling 50% Duty Cycle	$V_{IN} \geq V_{HC}$ $V_{IN} \leq 0.2V$
		1.8	5.0				$V_{IN} = 3.4V$ $V_{IN} = GND$
		3.0	8.0			(Note 5) $V_{CC} = \text{Max}$, Outputs Open $OE = GND, LE = V_{CC}$ $f_{CP} = 2.5 \text{ MHz}$ Eight Bits Toggling 50% Duty Cycle	$V_{IN} \geq V_{HC}$ $V_{IN} \leq 0.2V$
		5.0	14.5				$V_{IN} = 3.4V$ $V_{IN} = GND$
V_H	Input Hysteresis on LE only	200			mV		

Note 1: Maximum test duration not to exceed one second, not more than one output shorted at one time.

Note 2: This parameter guaranteed but not tested.

Note 3: Per TTL driven input ($V_{IN} = 3.4V$); all other inputs at V_{CC} or GND.

Note 4: This parameter is not directly testable, but is derived for use in Total Power Supply calculations.

Note 5: Values for these conditions are examples of the I_{CC} formula. These limits are guaranteed but not tested.

Note 6: $I_C = I_{QUIESCENT} + I_{INPUTS} + I_{DYNAMIC}$

$$I_C = I_{CC} + \Delta I_{CC} D_H N_T + I_{CCD} (f_{CP}/2 + f_i N_i)$$

I_{CC} = Quiescent Current

ΔI_{CC} = Power Supply Current for a TTL High Input ($V_{IN} = 3.4V$)

D_H = Duty Cycle for TTL inputs High

N_T = Number of Inputs at D_H

I_{CCD} = Dynamic Current caused by an Input Transition Pair (HLH or LHL)

f_{CP} = Clock Frequency for Register Devices (Zero for Non-Register Devices)

f_i = Input Frequency

N_i = Number of Inputs at f_i

All currents are in milliamperes and all frequencies are in megahertz.

Note 7: For 54FCT, $I_{CCD} = 0.40 \text{ mA/MHz}$.

Refer to applicable standard military drawing or NSC Table I for test conditions and I_C/I_{CC} limits.

AC Electrical Characteristics: See Section 2 for Waveforms

Symbol	Parameter	54/74FCT	74FCT		54FCT		Units	Fig. No.
		$T_A = +25^{\circ}C$ $V_{CC} = 5.0V$	$T_A, V_{CC} = \text{Com}$ $R_L = 500\Omega$ $C_L = 50 \text{ pF}$		$T_A, V_{CC} = \text{Mil}$ $R_L = 500\Omega$ $C_L = 50 \text{ pF}$			
		Typ	Min	Max	Min	Max		
t_{PLH} t_{PHL}	Propagation Delay D_n to O_n	5.0	1.5	8.0	1.5	8.5	ns	2-8
t_{PLH} t_{PHL}	Propagation Delay LE to O_n	9.0	2.0	13.0	2.0	15.0	ns	2-8
t_{PZH} t_{PZL}	Output Enable Time	7.0	1.5	12.0	1.5	13.5	ns	2-11
t_{PHZ} t_{PLZ}	Output Disable Time	6.0	1.5	7.5	1.5	10.0	ns	2-11
t_s	Setup Time High or Low, D_n to LE	1.0	2.0		2.0		ns	2-10
t_h	Hold Time High or Low, D_n to LE	1.0	1.5		1.5		ns	2-10
t_w	LE Pulse Width High or Low	5.0	6.0		6.0		ns	2-9

Note: Minimum limits are guaranteed but not tested on propagation delays.

Capacitance ($T_A = +25^\circ\text{C}$, $f = 1.0\text{ MHz}$)

Symbol	Parameter	Typ	Max	Units	Conditions
C_{IN}	Input Capacitance	6	10	pF	$V_{IN} = 0V$
C_{OUT}	Output Capacitance	8	10	pF	$V_{OUT} = 0V$

Note: This parameter is measured at characterization but not tested.

C_{OUT} for 74FCT only.